

Silicon PNP Power Transistors

2SA699 2SA699A

DESCRIPTION

- With TO-202 package
- Complement to type 2SC1226/1226A

APPLICATIONS

- Power amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

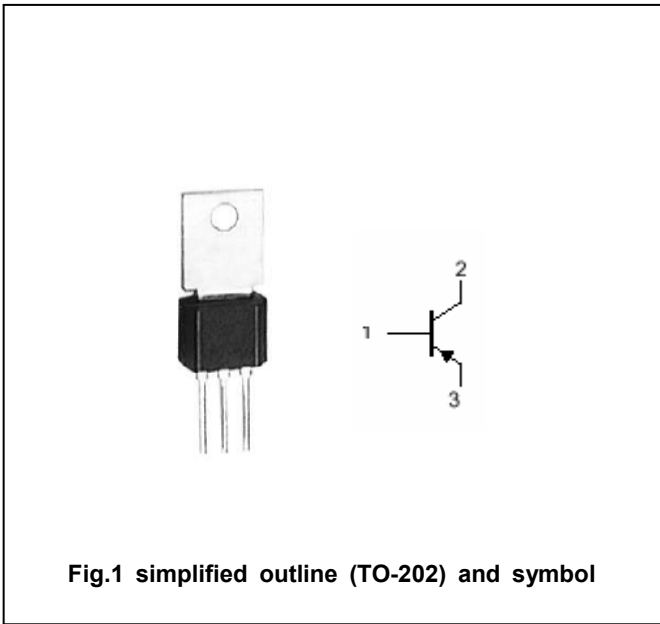


Fig.1 simplified outline (TO-202) and symbol

Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2SA699	-40	V
		2SA699A	-50	
V _{CEO}	Collector-emitter voltage	2SA699	-32	V
		2SA699A	-40	
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-2	A
I _{CM}	Collector current-peak		-3	A
I _B	Base current		-0.6	A
P _C	Collector power dissipation	T _C =25°C	10	W
T _J	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

Silicon PNP Power Transistors

2SA699 2SA699A

CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEsat}	Collector-emitter saturation voltage	I _C =-1.5A ; I _B =-0.15A		-0.4	-1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-2A ; I _B =-0.2 A			-1.5	V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-1mA; I _E =0	2SA699	-40		V
			2SA699A	-50		
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA; I _B =0	2SA699	-32		V
			2SA699A	-40		
I _{CBO}	Collector cut-off current	V _{CB} =-20V; I _E =0			-1	μA
I _{CEO}	Collector cut-off current	V _{CE} =-12V; I _B =0			-100	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-100	μA
h _{FE}	DC current gain	I _C =-1A ; V _{CE} =-5V	50		220	
C _{OB}	Output capacitance	I _E =0; V _{CB} =-5V; f=1MHz		70		pF
f _T	Transition frequency	I _E =0.5A ; V _{CB} =-5V		150		MHz

◆ h_{FE} classifications

P	Q	R
50-100	80-160	100-220

Silicon PNP Power Transistors

2SA699 2SA699A

PACKAGE OUTLINE

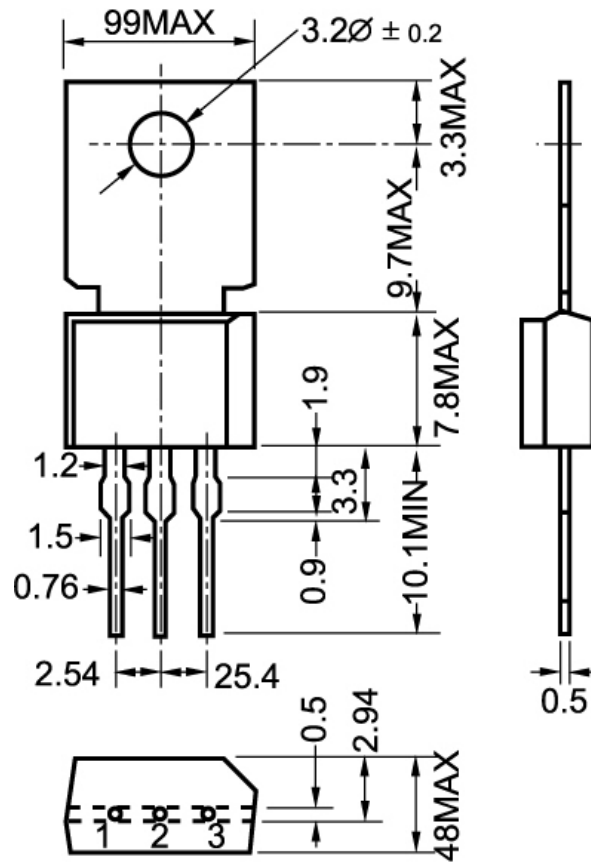
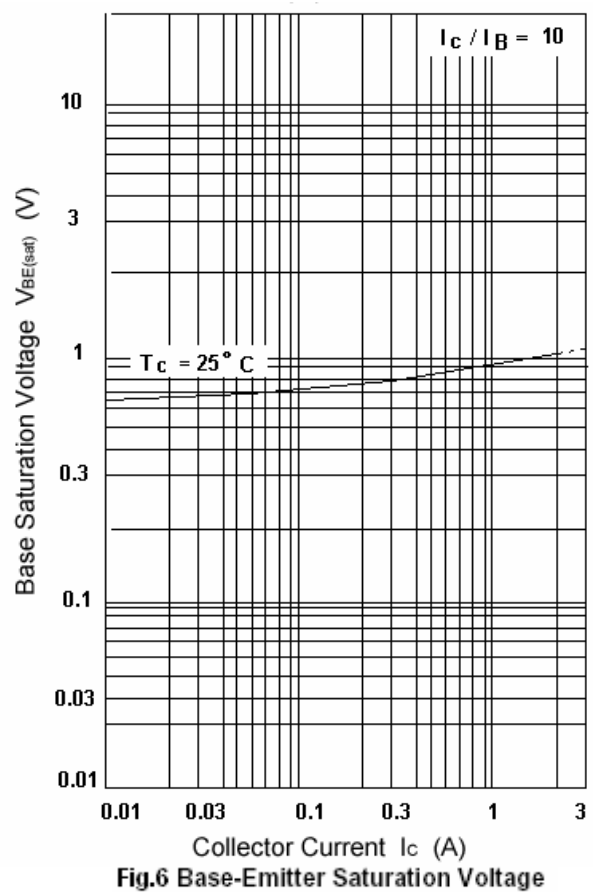
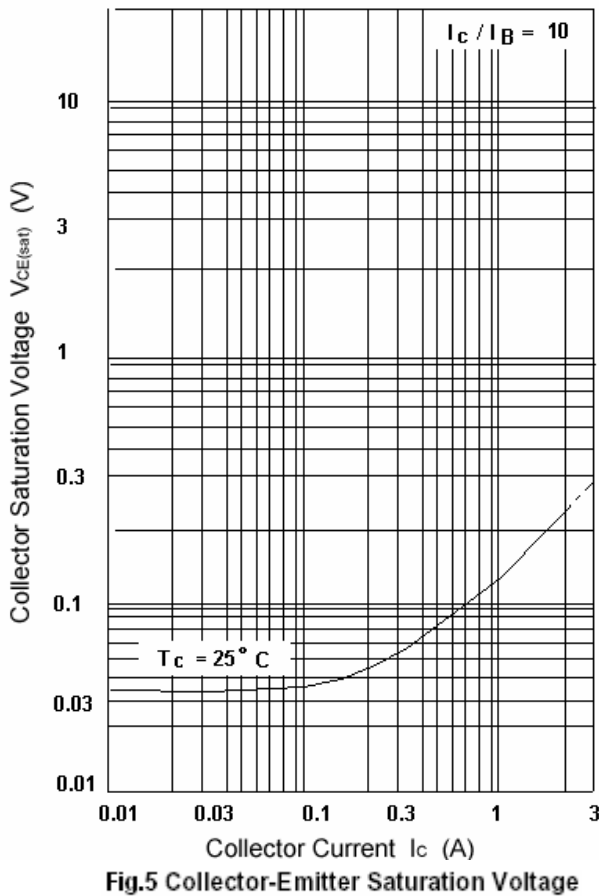
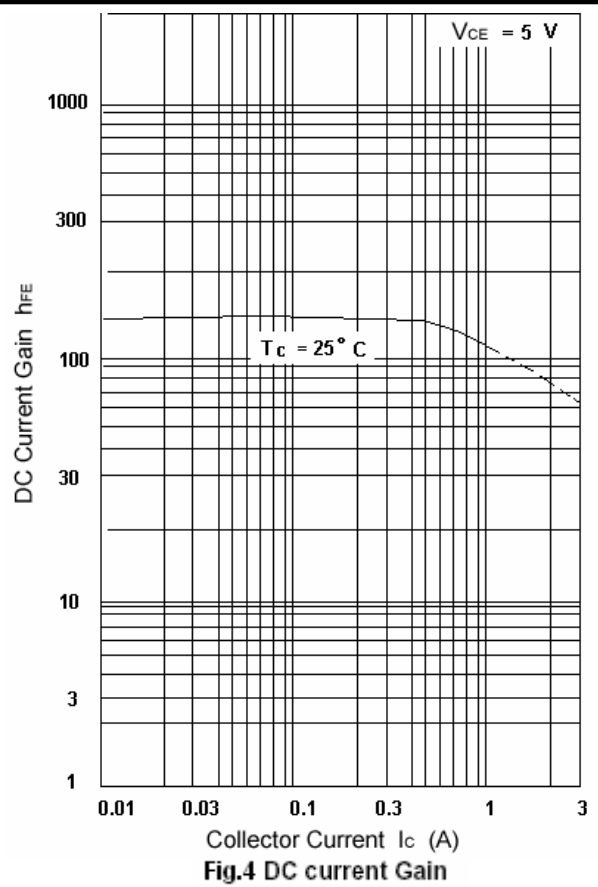
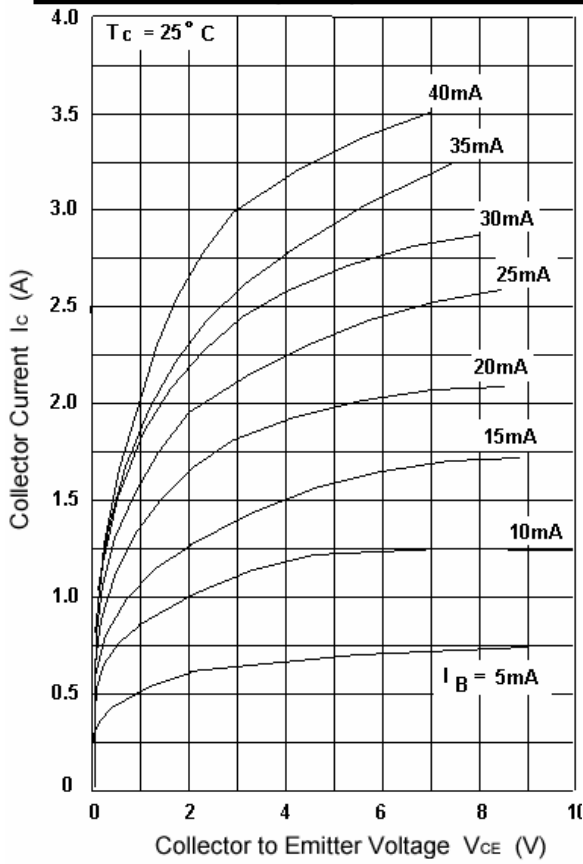


Fig.2 outline dimensions

Silicon PNP Power Transistors

2SA699 2SA699A



Silicon PNP Power Transistors

2SA699 2SA699A

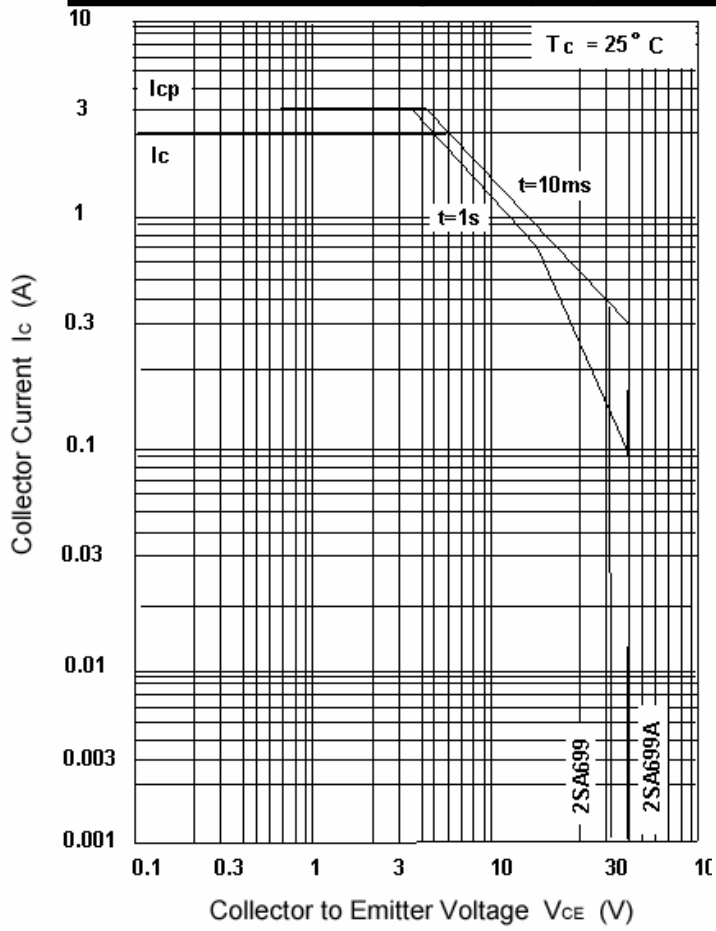


Fig.7 Safe Operating Area